

$$P \rightarrow l = 1$$

$$H_{SO} = \hbar \vec{L} \cdot \vec{S}$$

$$H_{SO} = \hbar \frac{A}{2} (j(j+1) - l(l+1) - s(s+1))$$

$$j^2, L^2, S^2 \rightarrow j_z$$

$$m, S_z \rightarrow \text{GOOD Q NUMBERS}$$

$$\vec{L} \cdot \vec{S} = L_x S_x + L_y S_y + L_z S_z$$

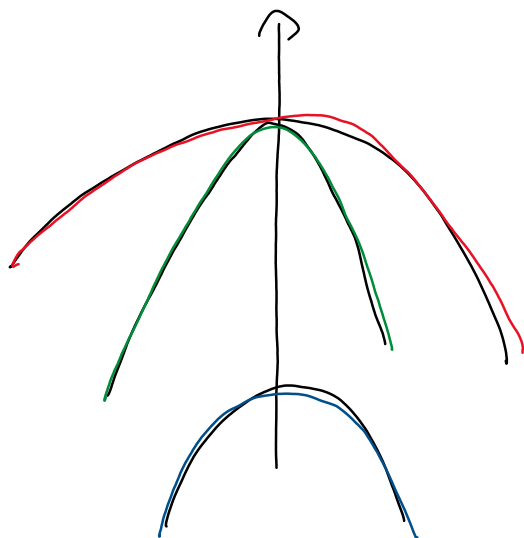
$$\leftarrow S_z$$

$$\leftarrow L_z$$

$$j = \frac{3}{2} \rightarrow \pm \frac{3}{2} j_z$$

$$j = \frac{1}{2} \rightarrow \pm \frac{1}{2} j_z$$

$$l = 1 \rightarrow \pm \frac{1}{2} j_z$$



$$H H \quad j = \frac{3}{2} \quad j_z = \pm \frac{3}{2}$$

$$L H \quad j = \frac{3}{2} \quad j_z = \pm \frac{1}{2}$$

$$S O \quad j = \frac{1}{2} \quad j_z = \pm \frac{1}{2}$$

Selection rules for interband transitions

The relevant matrix element is:

$$p_{if} = -i\hbar \int \psi_{\mathbf{k}_f \ell'}^* \nabla \psi_{\mathbf{k}_i \ell} d^3 r$$

$$\begin{aligned} |i\rangle &= \psi_{\mathbf{k}_i \ell} \\ &= e^{i\mathbf{k}_i \cdot \mathbf{r}} u_{\mathbf{k}_i \ell} \end{aligned}$$

$$\begin{aligned} |f\rangle &= \psi_{\mathbf{k}_f \ell'} \\ &= e^{i\mathbf{k}_f \cdot \mathbf{r}} u_{\mathbf{k}_f \ell'} \end{aligned}$$

HH↑, LH↑

≤ ↑

$$p_{if} = \hbar \mathbf{k}_i \int \psi_{\mathbf{k}_f \ell'}^* \psi_{\mathbf{k}_i \ell} d^3 r - i\hbar \int \underbrace{u_{\mathbf{k}_f \ell'}^* (\nabla u_{\mathbf{k}_i \ell})}_{\text{circled}} e^{i(\mathbf{k}_i - \mathbf{k}_f) \cdot \mathbf{r}} d^3 r$$

Zero since Bloch states are orthogonal

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Selection rules for interband transitions

- Conduction band:

$$u_{c0} = |s\rangle$$

where $|s\rangle$ is a spherically symmetric state.

- Valence band:

$$\text{Heavy hole states: } |3/2, 3/2\rangle = \frac{1}{\sqrt{2}} (|p_x\rangle + i|p_y\rangle) \uparrow$$

$$|3/2, -3/2\rangle = \frac{1}{\sqrt{2}} (|p_x\rangle - i|p_y\rangle) \downarrow$$

$$\text{Light hole states: } |3/2, 1/2\rangle = \frac{1}{\sqrt{6}} [(|p_x\rangle + i|p_y\rangle) \downarrow - 2|p_z\rangle \uparrow]$$

$$|3/2, -1/2\rangle = \frac{1}{\sqrt{6}} [(|p_x\rangle - i|p_y\rangle) \uparrow + 2|p_z\rangle \downarrow]$$

From symmetry we see that *only* the matrix elements of the form

$$\langle 3/2, 1/2 | \partial / \partial x | 3/2, 3/2 \rangle, \langle 3/2, 1/2 | \partial / \partial y | 3/2, 3/2 \rangle, \langle 3/2, 1/2 | \partial / \partial z | 3/2, 3/2 \rangle$$

$-\hbar^{-1} \langle s | \frac{\partial}{\partial x} | p_x \rangle = -\hbar^{-1} \langle s | \frac{\partial}{\partial y} | p_y \rangle = -\hbar^{-1} \langle s | \frac{\partial}{\partial z} | p_z \rangle = p_{cv}$
are different from zero.

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Selection rules for interband transitions

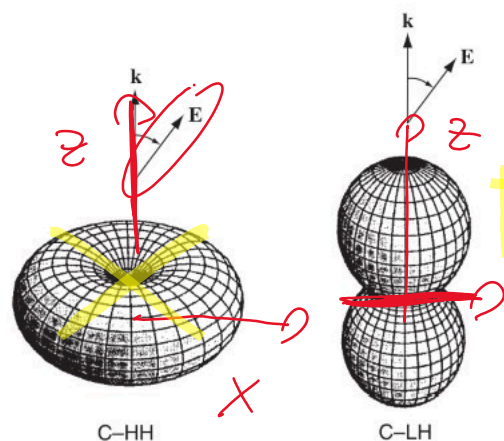
	VB HH → CB S	VB LH → CB S	
X pol	$\hbar^2 \langle s \frac{\partial}{\partial x} HH \rangle ^2 = \frac{1}{2} p_{cv}^2$	$\hbar^2 \langle s \frac{\partial}{\partial x} LH \rangle ^2 = \frac{1}{6} p_{cv}^2$	$\frac{1}{2} + \frac{1}{6}$
Y pol	$\hbar^2 \langle s \frac{\partial}{\partial y} HH \rangle ^2 = \frac{1}{2} p_{cv}^2$	$\hbar^2 \langle s \frac{\partial}{\partial y} LH \rangle ^2 = \frac{1}{6} p_{cv}^2$	$\frac{2}{3}$
Z pol	0	$\hbar^2 \langle s \frac{\partial}{\partial z} LH \rangle ^2 = \frac{2}{3} p_{cv}^2$	$\frac{2}{3} p_{cv}$

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Optical matrix element for HH and LH



HH states can be excited only by x,y polarized light

LH states can be excited by x,y and (predominantly) z polarized light

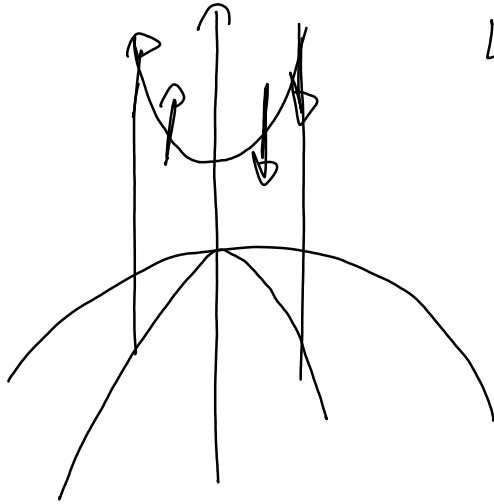
FIGURE A10.2: Dependence of the transition strength, $|M_T|^2$, on angle between the electron's k -vector and the incident electric field vector, E , for C-HH and C-LH transitions (C-S transitions are independent of angle). For C-HH transitions, $|M_T|^2$ is zero when

(C-SO transitions are independent of angle). For C-HH transitions, $|M_T|^2$ is zero when $\mathbf{E} \parallel \mathbf{k}$ and becomes a maximum of $\frac{1}{2} \times |M|^2$ when $\mathbf{E} \perp \mathbf{k}$. For C-LH transitions, when $\mathbf{E} \parallel \mathbf{k}$, $|M_T|^2$ has a peak value of $\frac{2}{3} \times |M|^2$ and is reduced to $\frac{1}{6} \times |M|^2$ when $\mathbf{E} \perp \mathbf{k}$.

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LINEARLY POL LIGHT

HH \uparrow S \uparrow HH \downarrow S \downarrow

LH \uparrow S \uparrow LH \downarrow S \downarrow

LH \downarrow S \uparrow LH \downarrow S \uparrow

Circularly polarized light

$$\vec{e} = \vec{e}_x \pm i \vec{e}_y \rightarrow \begin{cases} \vec{e}^+ & \text{CLOCKWISE} \\ \vec{e}^- & \text{ANTI-CLOCKWISE} \end{cases}$$

LIGHT POL

$$\text{HH } \uparrow \rightarrow \text{S } \uparrow \quad \vec{e}^+ - \vec{e} = \vec{e}_x + i \vec{e}_y$$

$$-i\hbar \left\langle -\frac{1}{\sqrt{2}} (\underline{P_x} + i \underline{P_y}) \uparrow \right| \underline{\frac{\partial}{\partial x}} + i \underline{\frac{\partial}{\partial y}} \left| \underline{\text{S } \uparrow} \right\rangle =$$

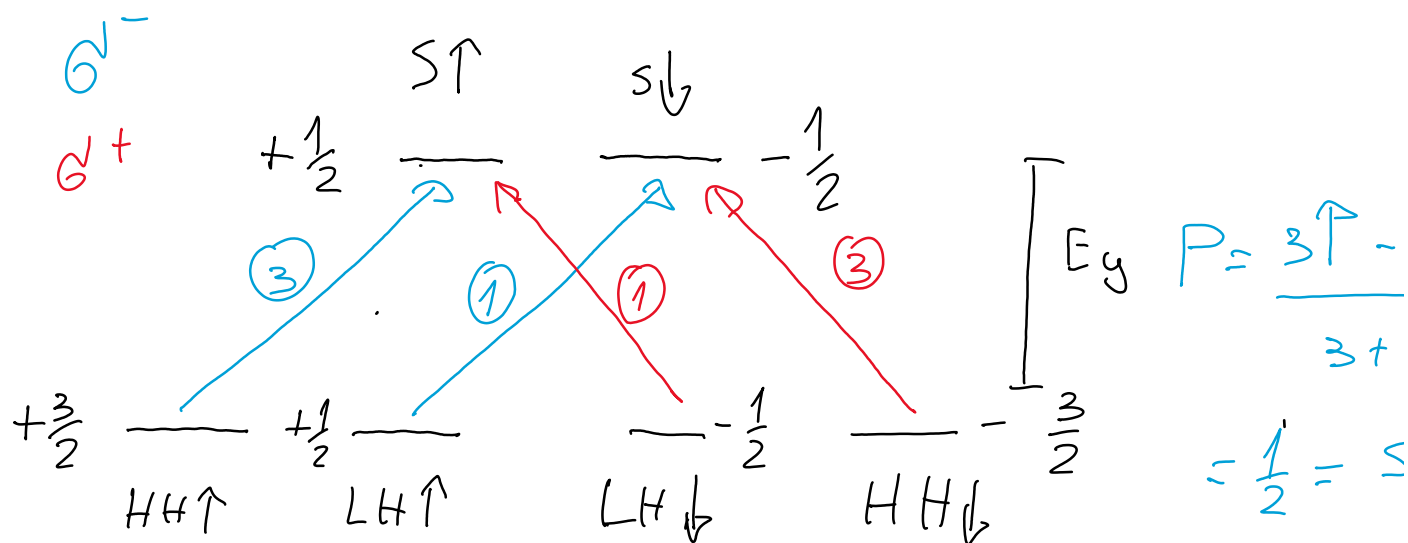
$$-\frac{1}{\sqrt{2}} P_{cv} - \frac{1}{\sqrt{2}} (-1) P_{cv} = 0$$

VIOLATING OF ANGULAR MOMENTUM

$$+\frac{3}{2}\hbar + \hbar \neq \frac{1}{2}\hbar \rightarrow \vec{e}^-$$

$$HH\uparrow + \frac{3}{2}\hbar - \hbar = \frac{1}{2}\hbar$$

$$LH\uparrow \quad \frac{1}{2}\hbar - \hbar = -\frac{1}{2}\hbar$$



$$6^- \quad HH\uparrow \rightarrow S\uparrow \quad 6^-$$

$$-i\hbar \nabla \cdot \frac{1}{\sqrt{2}} (P_x + iP_y) \uparrow \left| \frac{\partial}{\partial x} - i \frac{\partial}{\partial y} \right| S\uparrow \rangle =$$

$$- \frac{1}{\sqrt{2}} P_{cv} - \frac{1}{\sqrt{2}} P_{cv} = - \frac{2}{\sqrt{2}} P_{cv}.$$

$$|\langle A | \hat{x}^{\dagger} \cdot \vec{P} | i \rangle|^2 = 2 P_{cv}^2$$

$$LH\uparrow - S\downarrow$$

$$\frac{3}{2}, \frac{1}{2}$$

$$-i\hbar \nabla \cdot \frac{1}{\sqrt{6}} \left[(\underline{P_x + iP_y}) \underline{\downarrow} \cdot \underline{P_z \uparrow} \right] \left| \underline{\frac{\partial}{\partial x} - i \frac{\partial}{\partial y}} \right| \underline{S\downarrow},$$

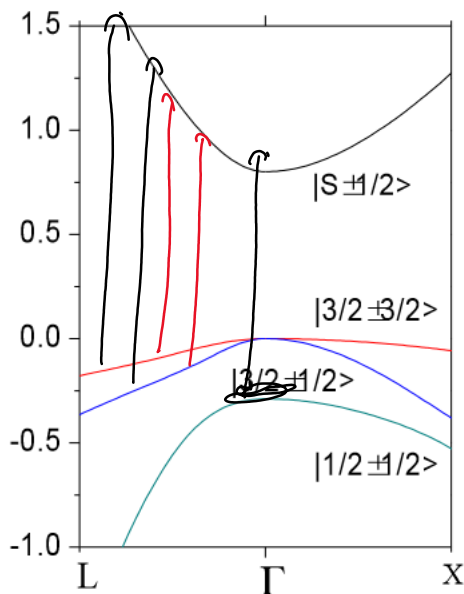
$$= - \frac{1}{\sqrt{6}} P_{cv} - \frac{1}{\sqrt{6}} P_{cv} = - \frac{2}{\sqrt{6}} P_{cv}$$

$$1 - \quad ,^2 \quad 2 \Delta^2$$

$$1.5 > 1 = \frac{2}{3} \times 1.5$$

$$\frac{HH\uparrow \rightarrow S\uparrow}{LH\uparrow \rightarrow S\downarrow} = \frac{2 P_{cv}^2}{\frac{2}{3} P_{cv}^2} = 3$$

Optical Spin Orientation



$$P = \frac{n_{\uparrow} - n_{\downarrow}}{n_{\uparrow} + n_{\downarrow}}$$

σ^- excitation
at Γ

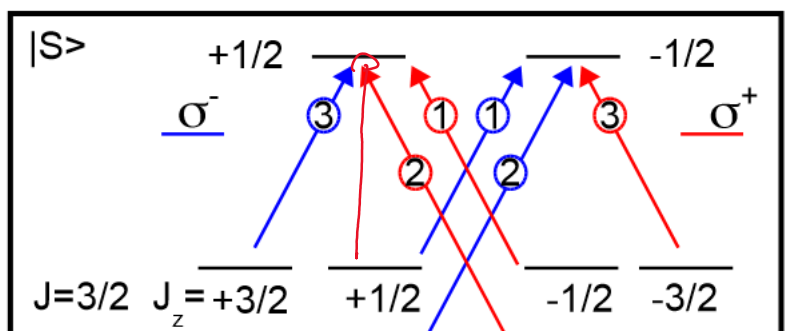
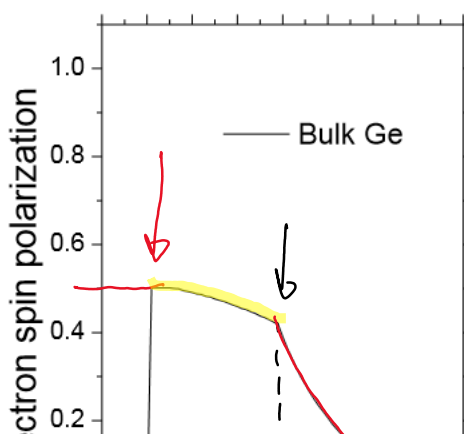
$$P = 0.5$$

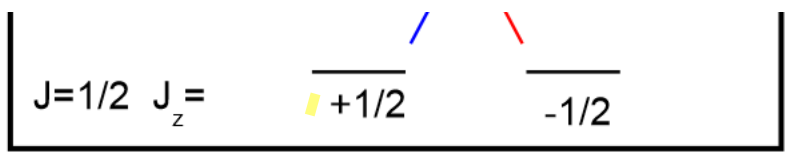
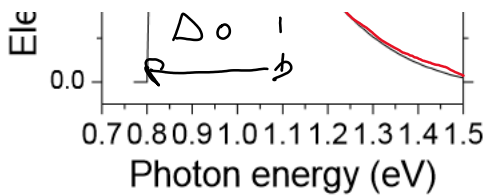
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Optical Spin Orientation





$$P = \frac{n_{\uparrow} - n_{\downarrow}}{n_{\uparrow} + n_{\downarrow}}$$

σ^- excitation
at Γ

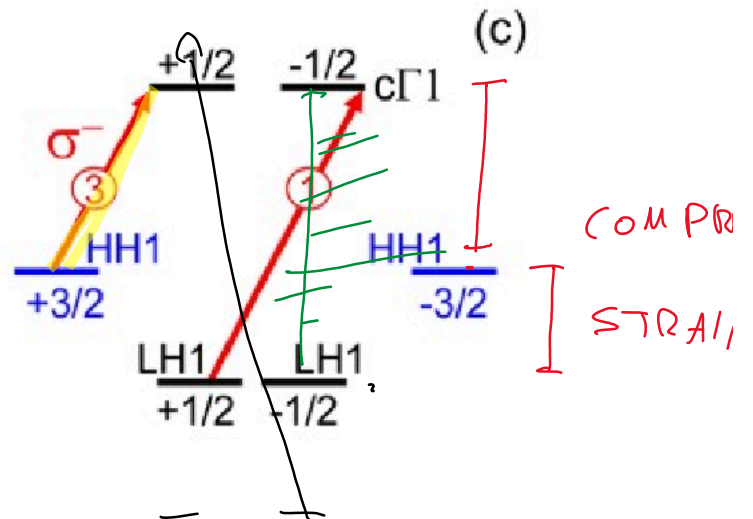
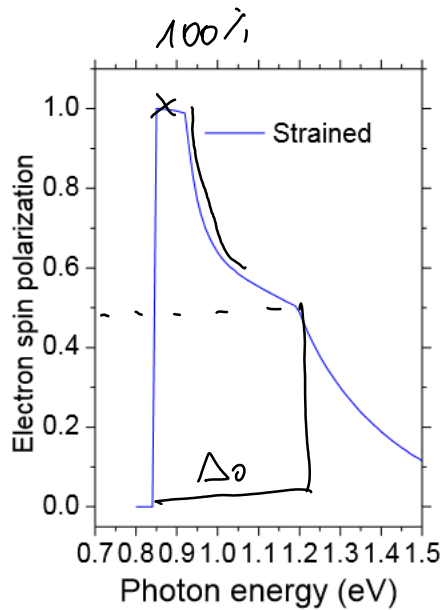
$$P = 0.5$$

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Optical Spin Orientation



$$P = \frac{n_{\uparrow} - n_{\downarrow}}{n_{\uparrow} + n_{\downarrow}}$$

σ^- excitation
at Γ

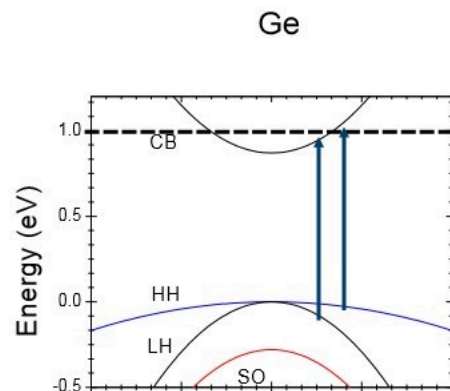
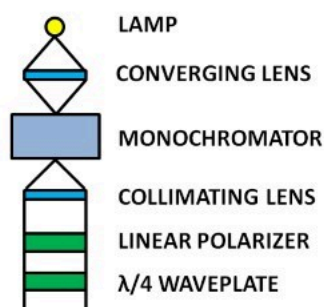
$$P = 1$$

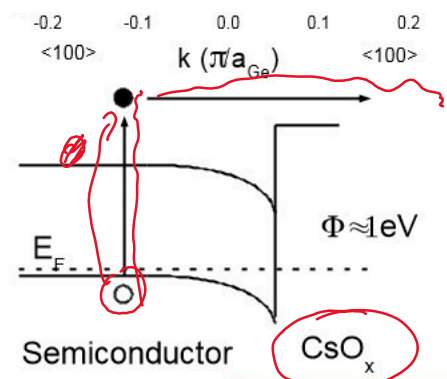
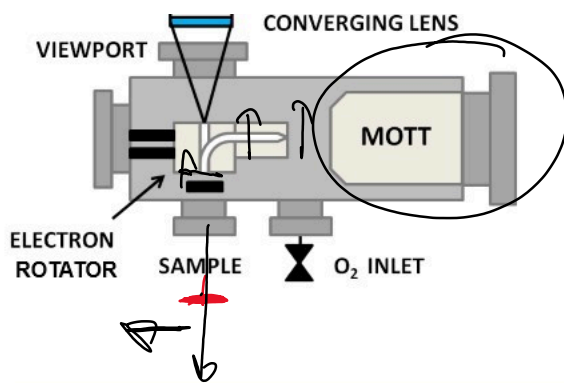
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Optical Spin Orientation: spin polarized photoemission

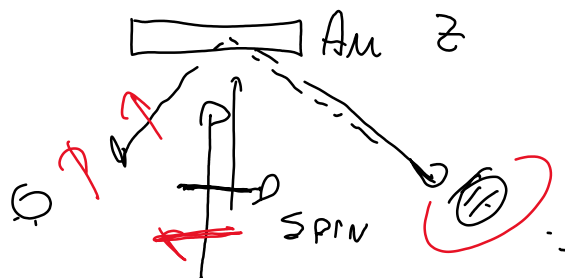




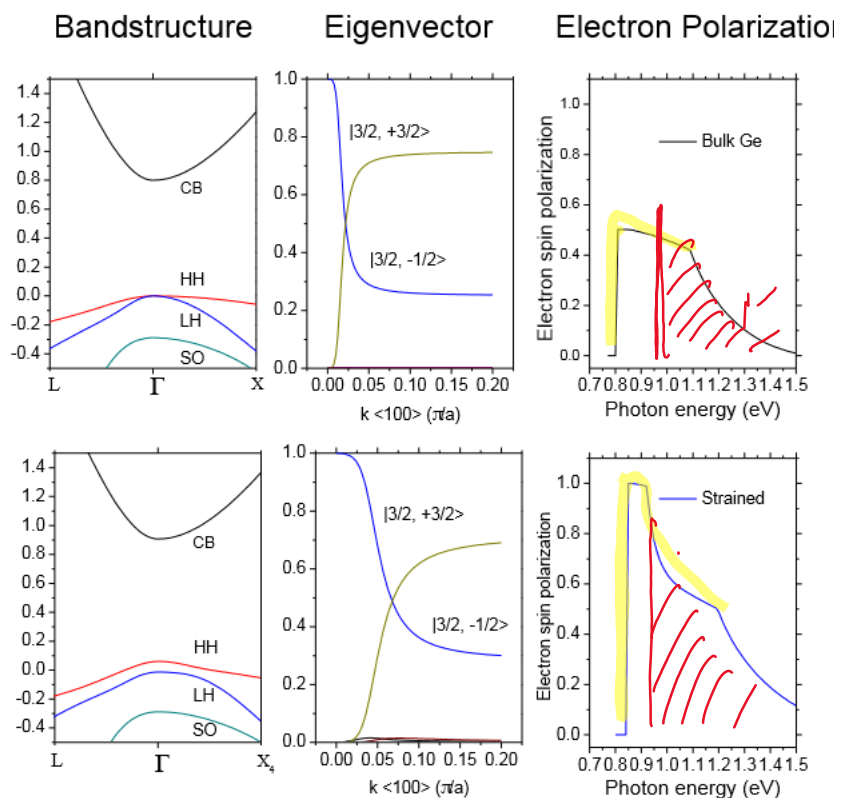
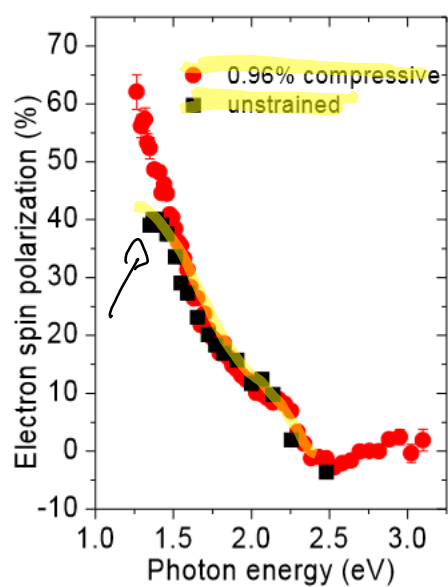
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Optical Spin Orientation: spin polarized photoemission

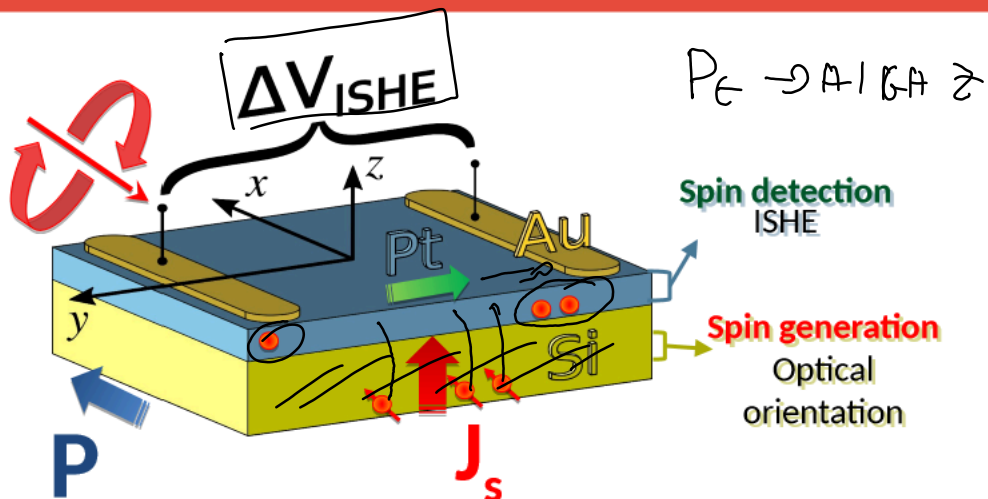


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Photo induced inverse spin Hall effect



$$\Delta V_{ISHE} \propto \gamma_{Pt} |J_s \times P|$$

Spin-to-charge
conversion

Spin
current

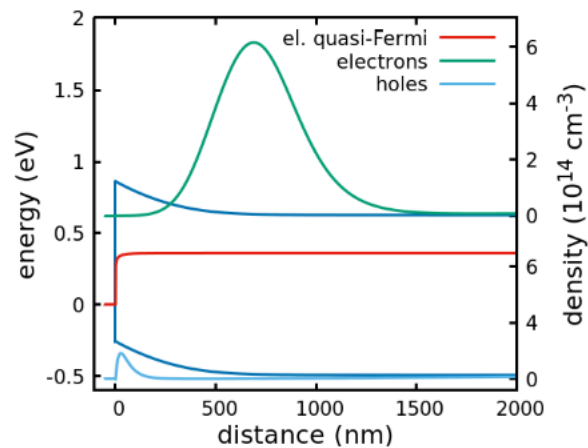
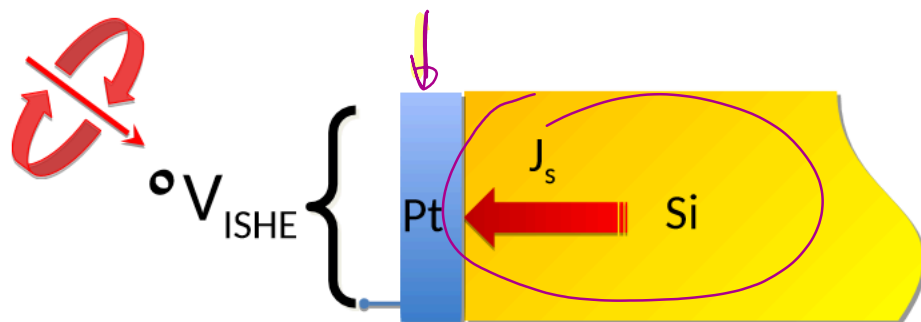
Spin
polarization

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Photo induced inverse spin Hall effect



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Photo induced inverse spin Hall effect

Charge drift-diffusion equations

<p>Current eq.</p> $J_n = -D_n \frac{\partial n}{\partial x} + \mu_n n E$ $J_p = -D_p \frac{\partial p}{\partial x} + \mu_p p E$	<p>Continuity eq.</p> $\frac{\partial J_n}{\partial x} = SRH + \Phi_0 \alpha e^{-\alpha x}$ $\frac{\partial J_p}{\partial x} = SRH + \Phi_0 \alpha e^{-\alpha x}$	<p>Poisson</p> $\frac{\partial E}{\partial x} = \frac{q}{\epsilon} (p + N_d - n)$ $SRH = w(x)(n_i^2 - np)$
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Spin drift-diffusion equations

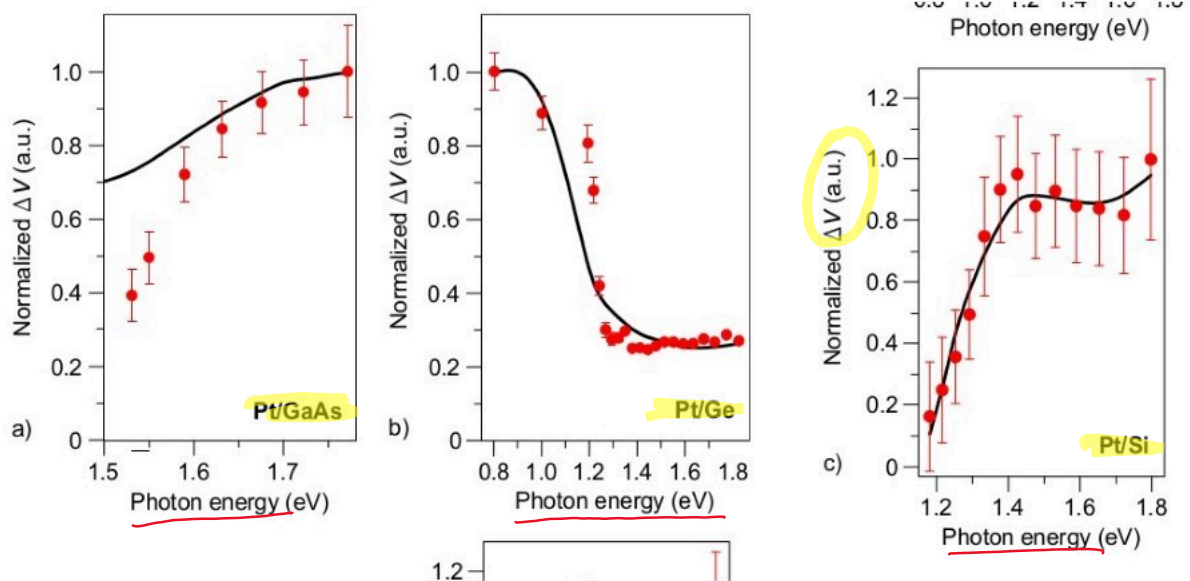
<p>Definitions</p> $s = n_+ - n_-$ $J_s = J_{n+} - J_{n-}$	<p>Current eq.</p> $J_s = -D_s \frac{\partial s}{\partial x} - \mu_s s E$	<p>Continuity eq.</p> $\frac{\partial J_s}{\partial x} = \frac{-s}{\tau_s} - w(sp) + P \Phi_0 \alpha e^{-\alpha x}$
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Photo induced inverse spin Hall effect

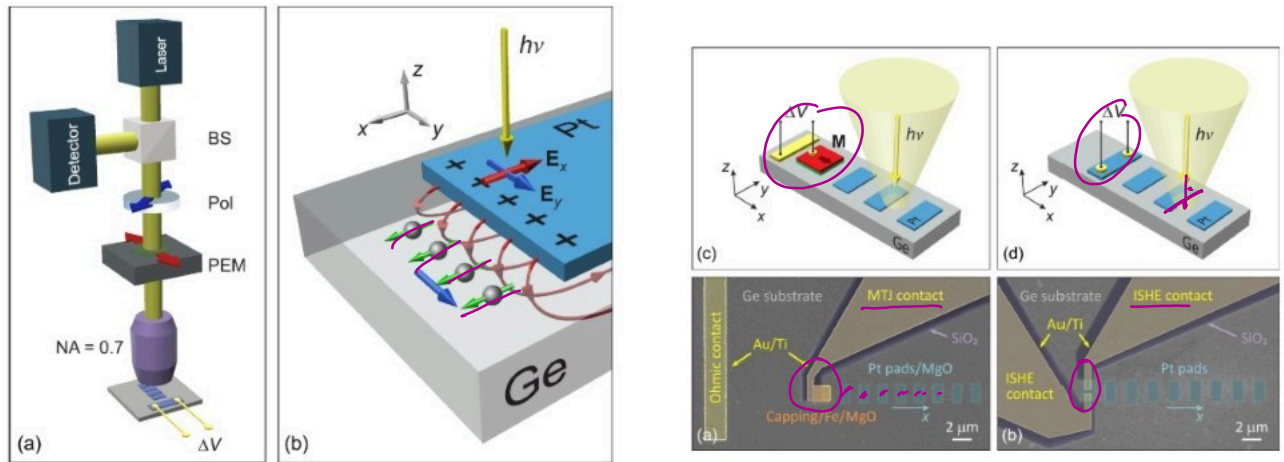


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Imaging spin diffusion



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Imaging spin diffusion

